

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

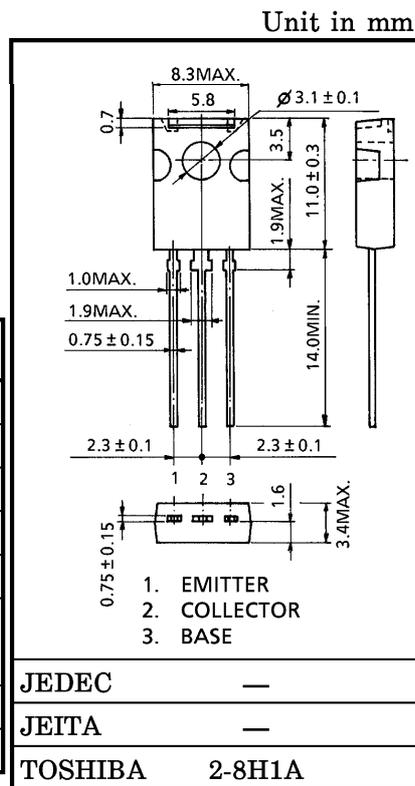
2SC3421

AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS

- Complementary to 2SA1358
- Suitable for Driver of 60 to 80 Watts Audio Amplifier
- High Breakdown Voltage

MAXIMUM RATINGS (T_c = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	120	V
Collector-Emitter Voltage	V _{CEO}	120	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	1	A
Base Current	I _B	100	mA
Collector Power Dissipation	P _C	T _a = 25°C	1.5
		T _c = 25°C	10
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Weight : 0.82g (Typ.)

ELECTRICAL CHARACTERISTICS (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 120V, I _E = 0	—	—	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 5V, I _C = 0	—	—	100	nA
Collector-Emitter Breakdown Voltage	V _{(BR) CEO}	I _C = 10mA, I _B = 0	120	—	—	V
DC Current Gain	h _{FE} (Note)	V _{CE} = 5V, I _C = 100mA	80	—	240	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 500mA, I _B = 50mA	—	0.30	1.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 5V, I _C = 500mA	—	0.78	1.0	V
Transition Frequency	f _T	V _{CE} = 5V, I _C = 100mA	—	120	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	15	—	pF

(Note) : h_{FE} Classification O : 80~160, Y : 120~240